



Dr. Saïd Agouram,

Graduated in Physics by the University of Moulay Ismail (MOROCCO) in 1998.

PhD by the University of Namur (BELGIUM) in 2003.

Scientific Research Technician at the SCSIE in the University of Valencia (SPAIN) from 2006.

Associate Professor at the Applied Physics Department of the University of Valencia (SPAIN) in 2010-2012 and 2015-...

He worked for a postdoctoral position at the Laboratoire de Physique des Matériaux Électroniques (Prof. Robert Sporken, Namur, Belgium). In October 2004, thanks to a grant from the foundation of the University of Valencia, he joined the group of Prof. Vicente Muñoz Sanjose and in 2006 he was hired as a researcher in the department of Applied Physics Department of the University of Valencia.

Since 2011 he is working at SCSIE of the University of Valencia as a specialist in high-resolution transmission electron microscopy (TEM). Dr. Saïd Agouram is also an Associate Professor in the Applied Physics Department of the University of Valencia and a member of CRECYCSEM research group directed by Prof. Vicente Muñoz Sanjose.

His main research is focused on crystal growth of semiconductor materials (by MOCVD, PVT and Spray Pyrolysis) and the study of structural and morphological properties of materials by high-resolution transmission electron microscopy (HRTEM). His publications belong to the field of crystal growth of semiconductor and characterization of materials. It is collaborating with several national and international research groups.

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